74LVC2G38

Dual 2-input NAND gate; open drain Rev. 10 — 28 June 2012

Product data sheet

General description 1.

The 74LVC2G38 provides a 2-input NAND function.

The outputs of the 74LVC2G38 devices are open-drain and can be connected to other open-drain outputs to implement active-LOW, wired-OR or active-HIGH wired-AND functions.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

Features and benefits 2.

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant outputs for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM EIA/JESD22-A114F exceeds 2000 V
 - MM EIA/JESD22-A115-A exceeds 200 V
- \pm 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Open-drain outputs
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC2G38DP	-40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74LVC2G38DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74LVC2G38GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1
74LVC2G38GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1 \times 0.5 mm	SOT1089
74LVC2G38GD	–40 °C to +125 °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3\times2\times0.5$ mm	SOT996-2
74LVC2G38GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body $1.6 \times 1.6 \times 0.5 \text{ mm}$	SOT902-2
74LVC2G38GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.2 \times 1.0 \times 0.35$ mm	SOT1116
74LVC2G38GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1.0 \times 0.35 mm	SOT1203

4. Marking

Table 2. Marking codes

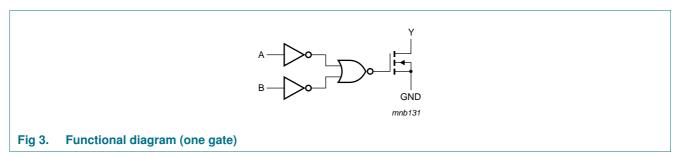
Type number	Marking code ^[1]
74LVC2G38DP	Y38
74LVC2G38DC	Y38
74LVC2G38GT	Y38
74LVC2G38GF	YB
74LVC2G38GD	Y38
74LVC2G38GM	Y38
74LVC2G38GN	YB
74LVC2G38GS	YB

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

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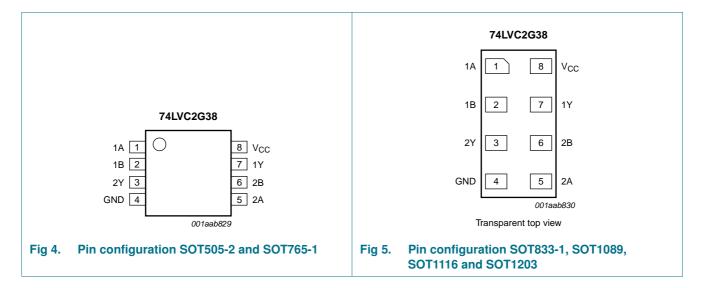
5. Functional diagram



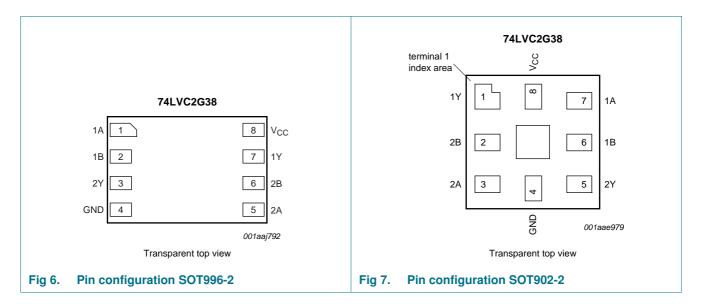


6. Pinning information

6.1 Pinning



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6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT505-2, SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2	
1A, 2A	1, 5	7, 3	data input
1B, 2B	2, 6	6, 2	data input
GND	4	4	ground (0 V)
1Y, 2Y	7, 3	1, 5	data output
V_{CC}	8	8	supply voltage

7. Functional description

Table 4. Function table[1]

Input		Output
nA	nB	nY
L	L	Z
L	Н	Z
Н	L	Z
Н	Н	L

^[1] H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF-state.

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					•
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+6.5	V
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
Vo	output voltage	Active mode	[<u>1][2]</u> _0.5	+6.5	V
		Power-down mode	[<u>1][2]</u> _0.5	+6.5	V
I _{IK}	input clamping current	$V_I < 0 V$	– 50	-	mA
lok	output clamping current	$V_O > V_{CC}$ or $V_O < 0 \text{ V}$	-	±50	mA
lo	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	<u>[3]</u> _	300	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		1.65	5.5	V
V_{I}	input voltage		0	5.5	V
Vo	output voltage	Active mode	0	V_{CC}	V
		disable mode	0	5.5	V
		Power-down mode	0	5.5	5.5 V 5.5 V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.65 \text{ V to } 2.7 \text{ V}$	-	20	ns/V
		$V_{CC} = 2.7 \text{ V to } 5.5 \text{ V}$	-	10	ns/V

^[2] When $V_{CC} = 0 \text{ V}$ (Power-down mode), the output voltage can be 5.5 V in normal operation.

^[3] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.
For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.
For XSON8, XSON8U and XQFN8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
T _{amb} = -	-40 °C to +85 °C[1]					
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	٧
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	٧
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	٧
		V _{CC} = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	٧
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{\text{CC}}$	٧
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	٧
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V V V V V V V V V V V V V V V V V V V
		V _{CC} = 4.5 V to 5.5 V	-	-	$0.3\times V_{\text{CC}}$	
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = 100 $\mu A;V_{CC}$ = 1.65 V to 5.5 V	-	-	0.1	٧
		$I_O = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	0.08	0.45	٧
		$I_O = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	0.14	0.3	٧
		$I_O = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	0.19	0.4	٧
		$I_O = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	0.37	0.55	٧
		$I_O = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.43	0.55	٧
I _I	input leakage current	$V_I = 5.5 \text{ V or GND}$; $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	±0.1	±5	μΑ
l _{OFF}	power-off leakage current	V_I or $V_O = 5.5 \text{ V}$; $V_{CC} = 0 \text{ V}$	-	±0.1	±10	μΑ
I _{CC}	supply current	V _I = 5.5 V or GND; V _{CC} = 1.65 V to 5.5 V; I _O = 0 A	-	0.1	10	μΑ
Δl _{CC}	additional supply current	per pin; $V_I = V_{CC} - 0.6 \text{ V}$; $I_O = 0 \text{ A}$; $V_{CC} = 2.3 \text{ V}$ to 5.5 V	-	5	500	μΑ
Cı	input capacitance		-	2.5	-	рF
T _{amb} = -	-40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	٧
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	٧
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	٧
		V _{CC} = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	٧
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{\text{CC}}$	٧
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	٧
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	٧
		V _{CC} = 4.5 V to 5.5 V	-	-	$0.3 \times V_{CC}$	V V V V V V V V V V V V V V V V V V V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 100 \ \mu A; \ V_{CC} = 1.65 \ V \ to \ 5.5 \ V$	-	-	0.1	٧
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.70	٧
		$I_O = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V V V V V V V V V V V V V V V V V V V
		$I_O = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.60	٧
		$I_O = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.80	V V V V V V V V V V V V V V V V V V V
		$I_O = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.80	٧
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Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	±20	μΑ
I _{OFF}	power-off leakage current	V_1 or $V_0 = 5.5 \text{ V}; V_{CC} = 0 \text{ V}$	-	-	±20	μΑ
I _{CC}	supply current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}; I_O = 0 \text{ A}$	-	-	40	μΑ
ΔI_{CC}	additional supply current	per pin; $V_1 = V_{CC} - 0.6 \text{ V}$; $I_O = 0 \text{ A}$; $V_{CC} = 2.3 \text{ V}$ to 5.5 V	-	-	5000	μА

^[1] All typical values are measured at T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		-40	°C to +85	°C	-40 °C to	o +125 °C	Unit
				Min	Typ[1]	Max	Min	Max	
	OFF-state to LOW	nA, nB to nY; see Figure 8							
	propagation delay	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.2	3.0	8.6	1.2	10.8	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	1.8	4.8	0.7	6.0	ns
		V _{CC} = 2.7 V		0.7	2.5	4.4	0.7	5.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		0.7	2.1	4.1	0.7	5.2	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.5	1.5	3.3	0.5	4.2	ns
t _{PLZ}	LOW to OFF-state	nA, nB to nY; see Figure 8							
	propagation delay	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.2	3.0	8.6	1.2	10.8	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	1.8	4.8	0.7	6.0	ns
		$V_{CC} = 2.7 \text{ V}$		0.7	2.5	4.4	0.7	5.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		0.7	2.1	4.1	0.7	5.2	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.5	1.5	3.3	0.5	4.2	ns
C_{PD}	power dissipation capacitance	per gate; $V_I = GND$ to V_{CC}	[2]	-	5	-	-	-	pF

^[1] Typical values are measured at nominal V_{CC} and at T_{amb} = 25 °C.

$$\Sigma(C_L \times V_{CC}^2 \times f_0) = \text{sum of outputs}.$$

^[2] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

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12. Waveforms

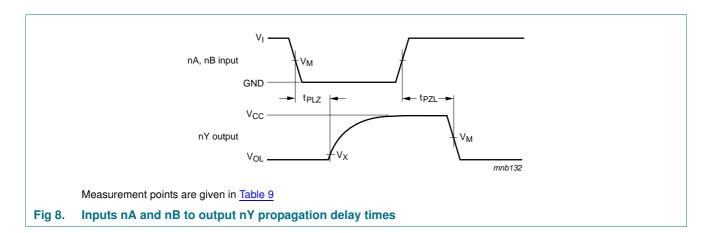
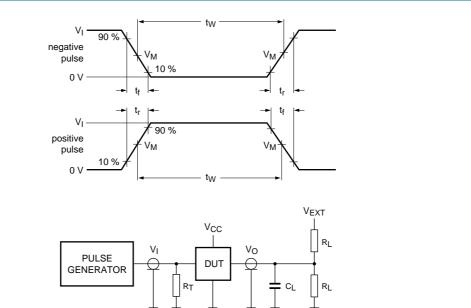


Table 9. Measurement points

Supply voltage	Input	Output				
V _{CC}	V _M	V _X	V _M			
1.65 V to 1.95 V	$0.5 \times V_{CC}$	V _{OL} + 0.15 V	$0.5 \times V_{CC}$			
2.3 V to 2.7 V	$0.5 \times V_{CC}$	V _{OL} + 0.15 V	$0.5 \times V_{CC}$			
2.7 V	1.5 V	V _{OL} + 0.3 V	1.5 V			
3.0 V to 3.6 V	1.5 V	V _{OL} + 0.3 V	1.5 V			
4.5 V to 5.5 V	$0.5 \times V_{CC}$	V _{OL} + 0.3 V	$0.5 \times V_{CC}$			

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Test data is given in Table 10

Definitions for test circuit:

 R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input		Load	Load				
V _{CC}	VI	t _r , t _f	CL	R _L	t _{PLZ} , t _{PZL}			
1.65 V to 1.95 V	V _{CC}	≤ 2.0 ns	30 pF	1 kΩ	$2 \times V_{CC}$			
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	$2 \times V_{CC}$			
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	6 V			
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	6 V			
4.5 V to 5.5 V	V _{CC}	≤ 2.5 ns	50 pF	500 Ω	$2 \times V_{CC}$			

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13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

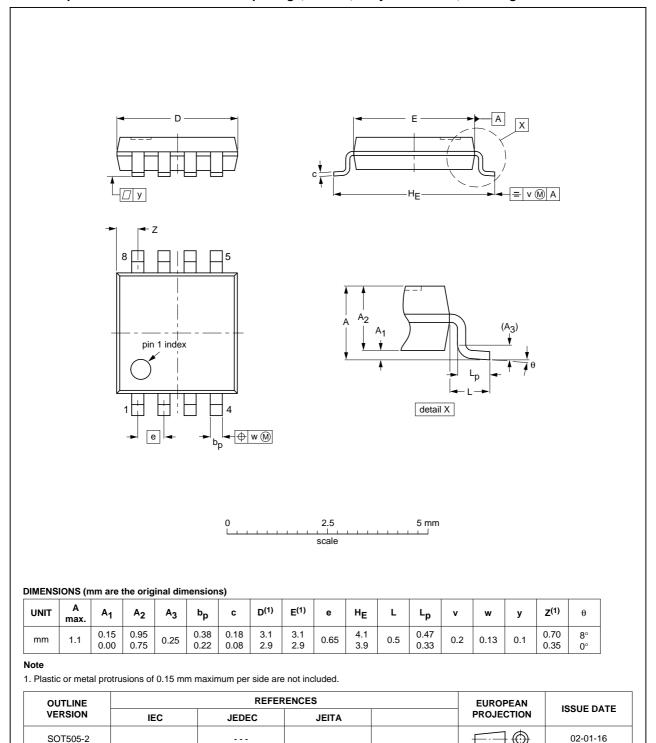


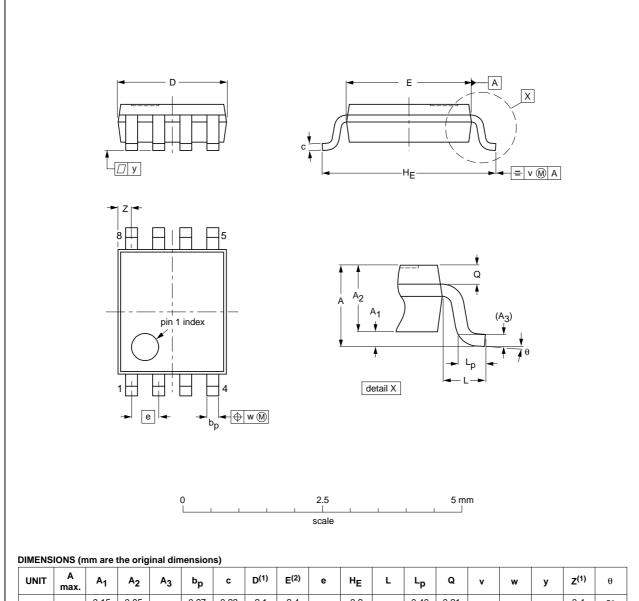
Fig 10. Package outline SOT505-2 (TSSOP8)

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VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A ₁	A ₂	А3	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT765-1		MO-187				02-06-07

Fig 11. Package outline SOT765-1 (VSSOP8)

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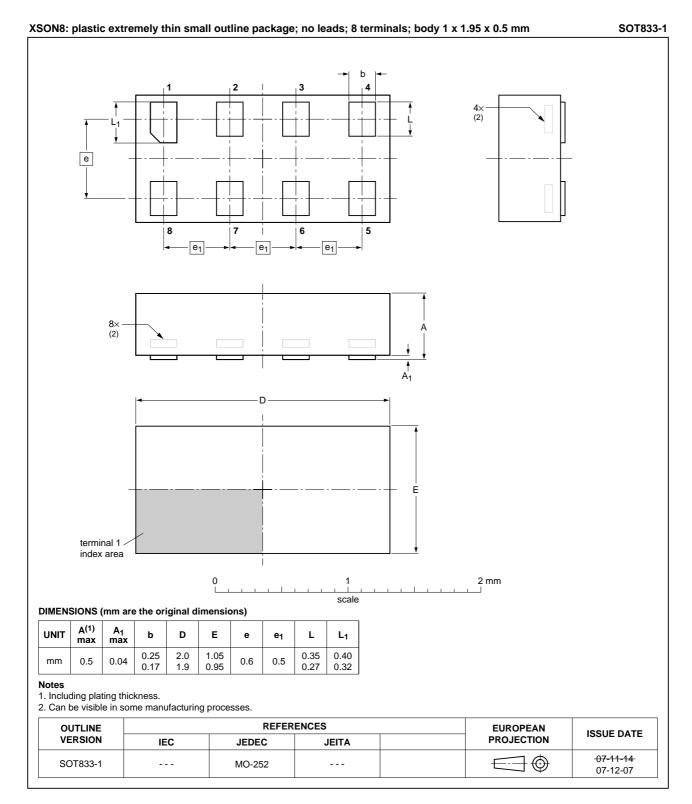


Fig 12. Package outline SOT833-1 (XSON8)

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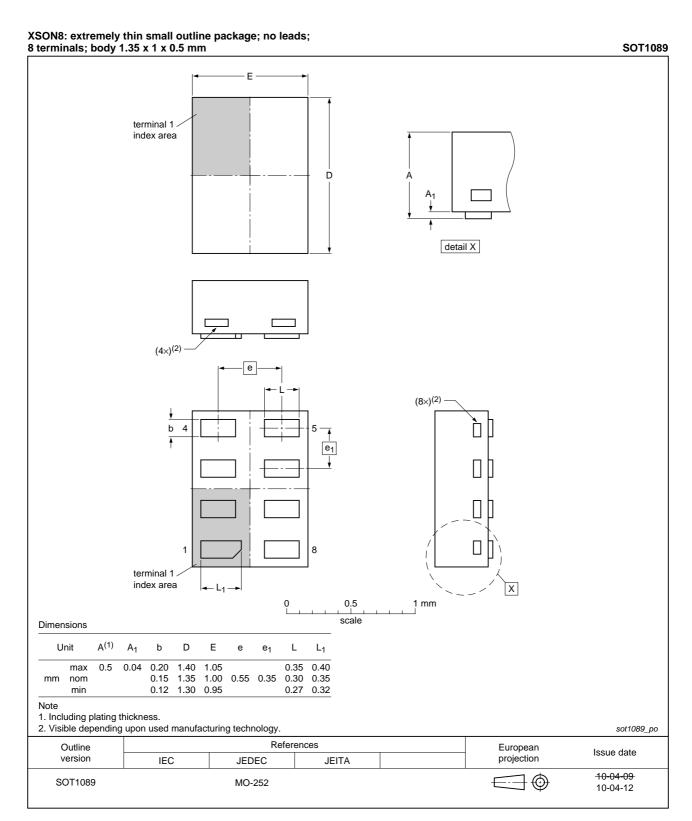


Fig 13. Package outline SOT1089 (XSON8)

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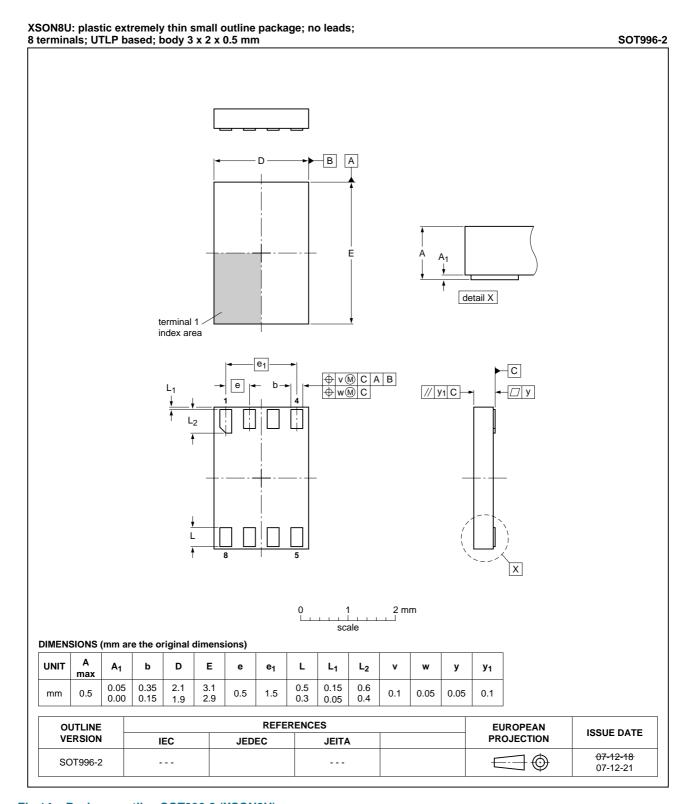


Fig 14. Package outline SOT996-2 (XSON8U)

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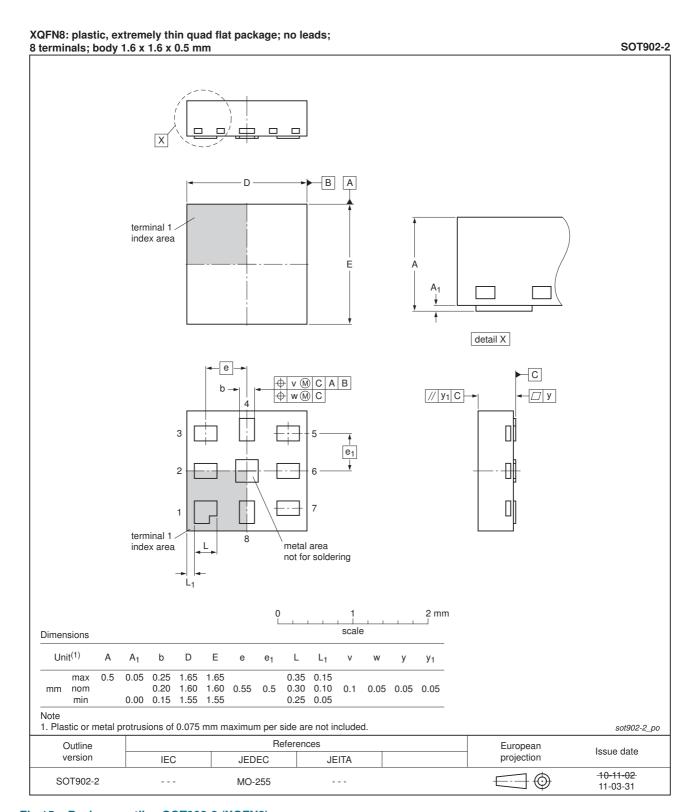


Fig 15. Package outline SOT902-2 (XQFN8)

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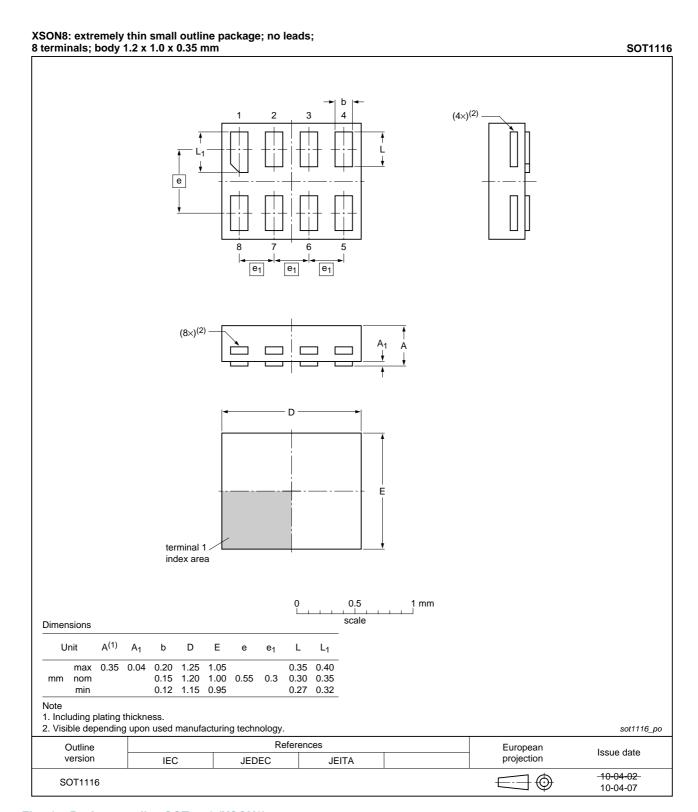


Fig 16. Package outline SOT1116 (XSON8)

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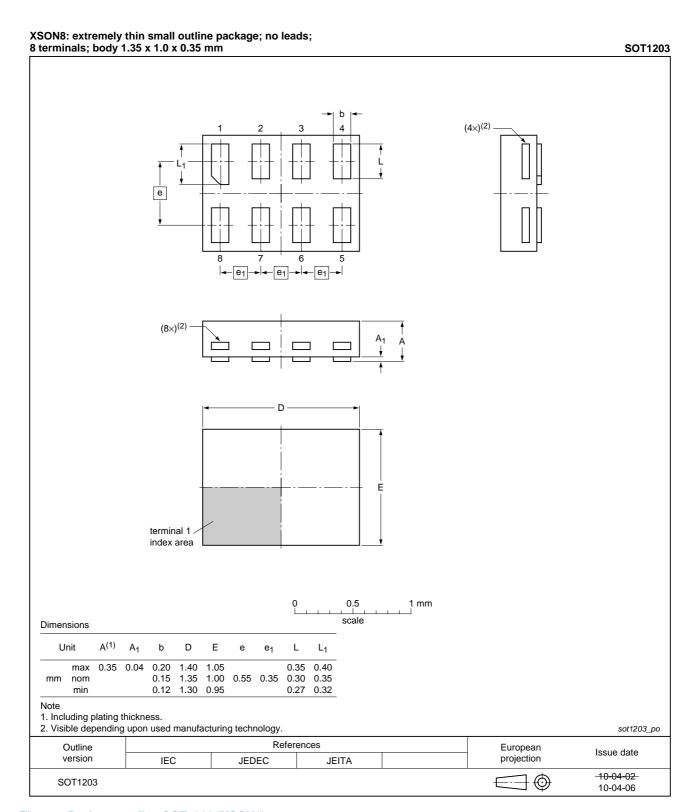


Fig 17. Package outline SOT1203 (XSON8)

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14. Abbreviations

Table 11. Abbreviations

Acronym	Description	
CMOS	Complementary Metal-Oxide Semiconductor	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
HBM	Human Body Model	
MM	Machine Model	
TTL	Transistor-Transistor Logic	

15. Revision history

Table 12. Revision history

	•			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC2G38 v.10	20120628	Product data sheet	-	74LVC2G38 v.9
Modifications:	 For type nu 	mber 74LVC2G38GM the S	OT code has changed t	o SOT902-2.
74LVC2G38 v.9	20111128	Product data sheet	-	74LVC2G38 v.8
Modifications:	 Legal pages 	s updated.		
74LVC2G38 v.8	20101104	Product data sheet	-	74LVC2G38 v.7
74LVC2G38 v.7	20090320	Product data sheet	-	74LVC2G38 v.6
74LVC2G38 v.6	20080219	Product data sheet	-	74LVC2G38 v.5
74LVC2G38 v.5	20070904	Product data sheet	-	74LVC2G38 v.4
74LVC2G38 v.4	20060516	Product data sheet	-	74LVC2G38 v.3
74LVC2G38 v.3	20050201	Product specification	-	74LVC2G38 v.2
74LVC2G38 v.2	20041018	Product specification	-	74LVC2G38 v.1
74LVC2G38 v.1	20031027	Product specification	-	-

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16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

16.2 Definitions

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